

reasonable assumptions that the highest operating frequency is inversely proportional to the system size and the current-level requirements of the logic circuits. An optimized design is presented for powering 16K circuits at an 80-percent duty cycle and a 1.7-ns logic cycle with maximum current levels of 300 mA.

To avoid lowering the systems lowest resonant frequency the power I/O line must be matched in impedance to the power source. In addition, to obtain a flat frequency response of the system currents to near the resonant frequency it is necessary to match the source impedance and the power I/O line impedance to the impedance of the primary windings of the highest level transformer. However, this may be undesirable because of the high supply-current level required. In the present design a mismatch was chosen—leading to a peaked response of the chip current as the lowest resonant frequency is approached and consequently, a lowering of the supply-current level.

This design of the power system will tolerate 5-percent variations in power-system line widths and insulation thickness at the cost of an additional skew of 1.2 percent of the logic cycle. (Actual tolerances achieved in this

technology are well within the 5-percent figure.) Some variation in logic load is tolerated provided the power lines are terminated in the prescribed manner.

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planar GaAs digital integrated circuit technology with gate densities and power dissipation levels compatible with LSI or VLSI.

Dr. Eden is a member of the American Physical Society, Eta Kappa Nu, Tau Beta Pi, Phi Kappa Phi, Phi Eta Sigma, Pi Mu Epsilon, and Sigma Xi.

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In 1967 he invented and developed the Mesh Emitter Transistor. Since 1972 he has been engaged in developing low-noise and power GaAs MESFET's, and GaAs FET logic circuits at Fujitsu Laboratories, Ltd. He holds 13 patents on semiconductor devices.

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Burton E. Dobratz was born in Janesville, WI, on May 30, 1936. He received the B.S.E.E. degree in 1959 and the M.S.E.E. degree in 1961, both from the University of California at Berkeley.

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emission, work he extended to surface state observations in silicon by vacuum photoemission and internal photoemission in MOS structures, after joining Rockwell International Science Center, Thousand Oaks, CA, in 1968. Following this, he carried out development work on high-speed high-efficiency heterojunction III-V alloy, $1.06 \mu\text{m}$ avalanche photodiodes, and an ultra-high sensitivity high-speed hybrid-integrated preamplifiers for these detectors. He was also involved in the design and analysis of a number of special device structures including the recently successfully demonstrated GaAs CCD. His most recent efforts have focused toward the development of a very high-speed, ultra low-power

Paul T. Greiling (S'64-M'69), for a photograph and biography please see p. 441 of this issue.

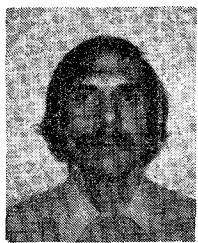
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H. L. Grubin (M'77) was born in Brooklyn, NY, on March 1, 1939. He was educated in New York City and received the Ph.D. degree from the Polytechnic Institute of New York, Brooklyn, in 1967.

He has been at United Technologies Research Center, East Hartford, CT, since 1966, where his studies center on hot carrier effects in semiconductor devices. He has numerous publications, including a monograph, in this area.

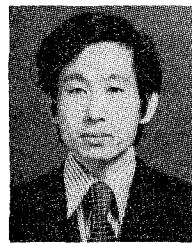
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Naoki Kato was born in Aichi, Japan, on July 11, 1949. He received the B.S. degree from Waseda University and the M.S. degree from Tokyo Metropolitan University.

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Mr. Kato is a member of the Japan Society of Applied Physics.

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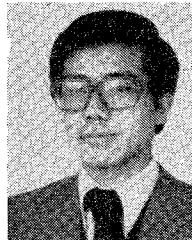


Charles F. Krumm, (S'65-M'69) was born in Macomb, IL on August 3, 1941. He received the BSE degree in 1963, the MSE degree in 1965, and the Ph.D degree in 1970, all in electrical engineering from the University of Michigan, Ann Arbor.

In 1969, he joined Raytheon Co., Research Division, Waltham, MA, as a Senior Scientist. There he was responsible for developing plated heat-sink Gunn-device technology and later low-noise and power GaAs FET's. This work led to the fabrication of the first integral beam lead power FET in 1975. In 1976 he joined Hughes Research Laboratories, Malibu, CA, as a Member of the Technical Staff. Initially he was responsible for fabrication of low noise FET's using electron beam lithography and this work led to the fabrication of the first 30-GHz FET amplifier. He is now Assistant Manager of the Electron Device Physics Department with responsibility for development of high-speed GaAs logic circuits and the supporting technology.

Dr. Krumm is a member of Eta Kappa Nu, Sigma Xi, and Phi Kappa Phi. He has served on the program committees for the International Electron Devices meeting and the Device Research Conference.

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Hirotsugu Kusakawa was born in Tokyo, Japan, on April 8, 1951. He received the B.S. degree in applied physics from Waseda University, Tokyo, Japan, in 1974.

In 1974 he joined the Semiconductor Laboratory, Fujitsu Laboratories, Ltd., Kawasaki, Japan, where he has been engaged in research and development of GaAs field-effect transistor devices and GaAs digital integrated circuit.

Mr. Kusakawa is a member of the Institute of Electronics and Communication Engineers of Japan.

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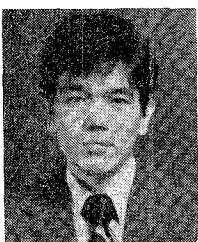


Frank S. Lee received the B.S. degree in electrical engineering from the National Cheng-Kung University, Taiwan, in 1971, and the M.S. and Ph.D. degrees in electrical engineering from Southern Methodist University, Dallas, TX, in 1974 and 1978, respectively. While pursuing the Ph.D. degree, he developed a group of low-pass filters by utilizing the properties of Cesaro summations to improve the convergence of infinite summations.

During 1974, he worked as a Research Assistant in the study of thermal electrical power and temperature coefficient of resistivity of Au-Ag alloy thin films. He is presently a member of the Technical Staff, Integrated Circuits Section, Rockwell International/Electronics Research Center, Thousand Oaks, CA. Here his work involves GaAs integrated circuit design, testing, and computer-aided circuit analysis.

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Masao Ida, photograph and biography not available at the time of publication.



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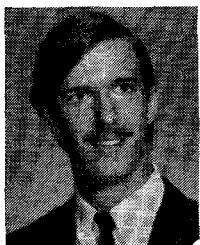


Stephen I. Long (S'73-M'73) received the B.S. degree in engineering physics from the University of California, Berkeley, in 1967, the M.S. and Ph.D. degrees in electrical engineering from Cornell University, Ithaca, NY, in 1969 and 1974, respectively. His thesis research dealt with steady-state liquid phase epitaxial growth of GaAs.

From 1969 to 1973, he served as a project engineer at the Rome Air Development Center, Griffiss Air Force Base, NY. There, he investigated and developed a steady-state liquid phase epitaxial growth process for thick, uniformly doped layers. From 1974 to 1977, he was a Senior Engineer and Manager of Semiconductor Engineering at Varian Associates, Palo Alto, CA, where he was involved in the development of vapor phase epitaxial growth of GaAs and InP, design and development of high-efficiency GaAs IMPATT devices, millimeter wave InP Gunn devices, and project management. In 1978, he joined the Rockwell International Science Center, Thousand Oaks, CA, and is currently a Project Leader in the integrated circuit group. His work involves design and evaluation of GaAs integrated circuits.

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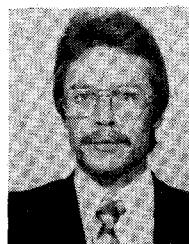
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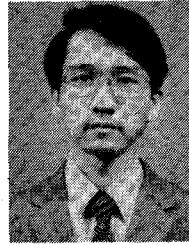
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He joined the Thomson-CSF, Central Research Laboratory in 1976. He is currently involved with the design and evaluation of high speed GaAs integrated circuits.

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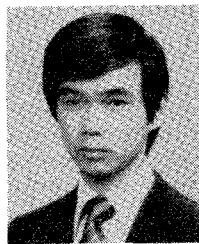
He was employed by Stavid Engineering, Inc., Plainfield, NJ, for the installation and maintenance of electronic flight simulation equipment

from 1947 to 1950. During 1954 and 1955 he was a member of the M.S. Fellowship Plan of Hughes Aircraft Co., and served there as a Member of the Technical Staff until 1957. His work included radar systems and circuit studies, weapons systems analyses, and the development of an electron trajectory computer. In 1960 he was appointed Acting Assistant Professor of electrical engineering at the University of California, Berkeley. During 1960-1961 he was at the Technische Hochschule, Vienna, Austria, as a National Science Foundation Post-Doctoral Fellow. He returned to Berkeley as an Assistant Professor in 1961, and engaged in research in noise and focusing in crossed-field electron-beam amplifiers. During 1965-1966 he taught electromagnetic field theory and initiated a laser research project at the Catholic University of Chile, Santiago, as a part of a Ford Foundation program. He spent 1969-1970 at Rutgers University and Bell Telephone Laboratories in research on superconductivity. He was a visiting Professor at Kyoto University and University of Paris during 1977-1978. He is currently a Professor at Berkeley where he is engaged in teaching and research in solid-state devices and superconductivity. His current research emphasis is on Josephson devices and their applications. He has published numerous papers on electron devices, is coauthor (with S. Ramo and J. R. Whinnery) of *Fields and Waves in Communications Electronics*, and is author and principal of an educational film, "Wave Velocities, Dispersion, and the ω - β Diagram."

Dr. Van Duzer is a member of Eta Kappa Nu, Tau Beta Pi, and Sigma Xi.

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Naoki Yokoyama (M'78) was born in Osaka, Japan, on March 28, 1949. He received the B.S. degree in physics from Osaka City University and the M.S. degree in physics from Osaka University, Osaka, Japan, in 1971 and 1973, respectively.

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R. Zucca (SM'78) was born in Trieste, Italy, on February 7, 1936. He received the M.S. degree in engineering from the University of Rosario, Argentina, in 1960, and the Ph.D. degree in physics from the University of California, Berkeley, in 1971.

He initiated his research at Berkeley in the investigation of optical properties of solids by modulation techniques. This work which involved the construction of a wavelength modulation spectrometer with a very broad spectral range (1.75-6 eV), contributed to better understanding of the band structures of IV and III-V semiconductors, and noble metals. Later he held a position of Professor (in physics) at the University at Rosario, Argentina, where he continued his research in optical properties of solids in association with the University of California, Berkeley. Since joining Rockwell International, Thousand Oaks, CA, in 1972, he has been engaged in several aspects of semiconductor technology, focusing mainly on the electrical properties of semi-insulating GaAs, the substrate material for most GaAs high-frequency semiconductor devices. A major accomplishment in this area was the development of a model for the electrical compensation in semi-insulating GaAs. Most recently he has been involved in the development of a high-speed low-power planar GaAs digital IC technology with potential for LSI/VLSI applications. His work involves the development and application of testing techniques for process characterization and evaluation.

Dr. Zucca is a member of the American Physical Society.



Bryant M. Welch (M'75) was born in New York, NY, on December 20, 1943. He received the A.A. degree in engineering from Miami Dade Junior College, Miami, FL in 1963 and a B.S. degree in mathematics from California State University, Northridge, in 1968.

From 1963 to 1965 he was associated with Westinghouse Electric Corporation, where he was involved in the early development of Si bipolar integrated circuits. Since 1965 he has been employed with Rockwell International, Thousand Oaks, CA, and is presently the Project Leader for integrated circuit processing. His areas of research and development have included all phases of ion implantation in both Si and GaAs. Since 1972, he has concentrated on the development of a planar GaAs ion implantation technology. Highlights of his work include the development and fabrication of GaAs FET's, using implanted active layers, and fabrication of the first planar GaAs integrated circuits using multiple localized implanta-

tion techniques. He is currently involved with developing planar GaAs integrated circuit processes and responsible for the fabrication of these circuits. He holds two patents and has numerous publications in the field of ion implantation and its applications.